Abstract of the Disclosure

A PMOS transistor is formed in a CMOS integrated circuit, having a $Si_{1-x}Ge_x/Si$ heterojunction between the channel region and the substrate. The method is applicable to large volume CMOS IC fabrication. Germanium is implanted into a silicon substrate, through a gate oxide layer. The substrate is then annealed in a low temperature furnace, to form $Si_{1-x}Ge_x$ in the channel region.

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